

FEATURES

- **HIGH OUTPUT POWER:** 1 W
- **HIGH LINEAR GAIN:** 9.0 dB
- **HIGH EFFICIENCY:** 37% (PAE)
- **INDUSTRY STANDARD PACKAGING**
- **THIS DEVICE IS ALSO AVAILABLE AS A TWO-CELL CHIP: NE8500100**

DESCRIPTION

The NE8500199 is a medium power GaAs MESFET designed for up to a 1W output stage or as a driver for higher power devices. The device has no internal matching and can be used at frequencies from UHF to 8.5 GHz. The device is available in the "99" package or in chip form. The chip is a two-cell die; bonding both cells delivers the rated performance.

The NE850 Series Transistors are manufactured to NEC's stringent quality assurance standards to ensure highest reliability and consistent superior performance.

ABSOLUTE MAXIMUM RATINGS¹

(T_c = 25 °C unless otherwise noted)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{DS}	Drain to Source Voltage	V	15
V _{GD}	Gate to Drain Voltage	V	-18
V _{GS}	Gate to Source Voltage	V	-12
I _{DS}	Drain Current	A	IDSS
I _{GS}	Gate Current	mA	6.0
P _T	Total Power Dissipation	W	6.0
T _{CH}	Channel Temperature	°C	175
T _{STG}	Storage Temperature	°C	-65 to +175

Note:

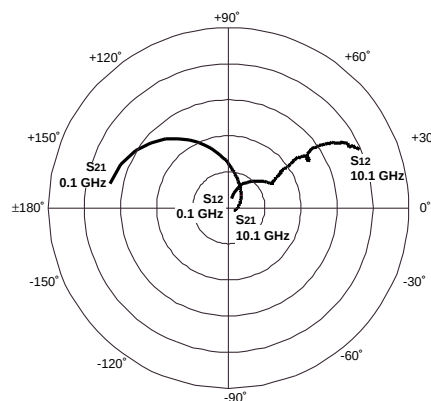
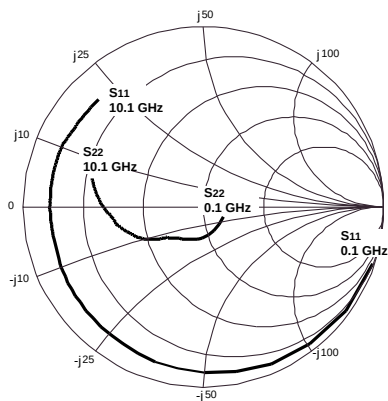
1. Operation in excess of any one of these parameters may result in permanent damage.

RECOMMENDED OPERATING LIMITS

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
V _{DS}	Drain to Source Voltage	V	9		10
T _{CH}	Channel Temperature	°C			130
G _{COMP}	Gain Compression	dB			3.0
R _G	Gate Resistance	KΩ		1	4

ELECTRICAL CHARACTERISTICS (T_c = 25°C)

PART NUMBER				NE8500199 NE8500100 00 (Chip), 99			TEST CONDITIONS
PACKAGE OUTLINE				MIN	TYP	MAX	
Functional Characteristics	SYMBOLS	CHARACTERISTICS	UNITS				P _{IN} = 21.0 dBm f = 7.2 GHz V _{DS} = 10 V; I _{DSQ} = 200 mA R _G = 1KΩ
	P _{OUT}	Power Out at Fixed Input Power	dBm	28.5	29.5		
	G _L	Linear Gain	dB		9.0		
	η _{ADD}	Collector Efficiency	%		37		
Electrical DC Characteristics	I _{DS}	Drain Source Current	mA		200		V _{DS} = 2.5 V; V _{GS} = 0 V
	I _{DSS}	Saturated Drain Current	mA	330		825	
	V _P	Pinch-off Voltage	V	-3.0		-1.0	V _{DS} = 2.5 V; I _{DS} = 4 mA
	g _m	Transconductance	mS		300		V _{DS} = 2.5 V; I _{DS} = I _{DSS}
	R _{TH}	Thermal Resistance	°C/W			60	Channel to Case

TYPICAL SCATTERING PARAMETERS (T_A = 25 °C)

S₂₁ MAG:
4.0 / DIV., 20.0 FS
S₁₂ MAG:
0.03 / DIV., 0.15 FS

NE 8500100 (2 Cells)
V_{DS} = 10 V, I_{DS} = 200 mA

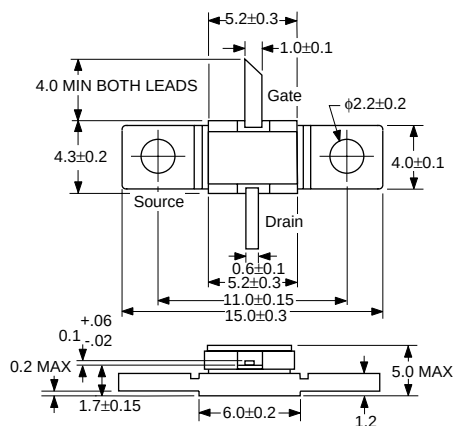
FREQUENCY	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹
GHZ	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)
0.10	0.990	-18.400	13.477	168.400	0.008	74.200	0.122	-27.200	0.107	32.265
0.20	0.981	-36.000	12.933	158.100	0.013	72.500	0.131	-49.100	0.102	29.978
0.50	0.933	-78.900	10.387	132.500	0.026	53.300	0.171	-92.100	0.209	26.015
1.00	0.884	-120.400	6.899	106.600	0.036	37.500	0.210	-121.500	0.378	22.825
1.50	0.865	-142.100	4.970	90.700	0.040	30.700	0.235	-132.500	0.533	20.943
2.00	0.859	-155.700	3.842	79.200	0.041	28.100	0.258	-138.400	0.689	19.718
2.50	0.850	-164.900	3.083	69.600	0.043	31.000	0.278	-141.400	0.871	18.555
3.00	0.850	-172.000	2.554	60.300	0.045	32.300	0.302	-144.100	0.985	17.540
3.50	0.850	-178.000	2.224	52.100	0.049	33.400	0.330	-146.900	1.010	15.948
4.00	0.852	-176.900	1.942	45.400	0.052	33.100	0.355	-149.800	1.048	14.384
4.50	0.853	-172.600	1.704	38.600	0.057	35.700	0.382	-152.700	1.056	13.303
5.00	0.854	-168.400	1.501	29.500	0.060	34.900	0.409	-156.300	1.083	12.227
5.50	0.854	-164.500	1.383	22.900	0.064	35.800	0.433	-160.000	1.070	11.727
6.00	0.854	-161.000	1.256	18.200	0.070	36.000	0.457	-163.600	1.048	11.197
6.50	0.854	-157.500	1.133	11.900	0.077	34.300	0.481	-167.400	1.007	11.166
7.00	0.850	-153.800	1.048	3.800	0.077	30.300	0.502	-171.600	1.063	9.803
7.50	0.842	-150.700	0.968	-0.400	0.078	33.300	0.521	-175.000	1.204	8.207
8.00	0.839	-147.700	0.877	-4.800	0.085	35.700	0.546	-178.400	1.213	7.348
8.50	0.836	-144.600	0.811	-11.800	0.093	34.200	0.568	-177.800	1.152	7.037
9.00	0.833	-141.500	0.774	-17.600	0.102	32.400	0.592	-174.100	1.046	7.486
9.50	0.834	-138.200	0.723	-21.500	0.111	29.100	0.613	-170.300	0.962	8.138
10.00	0.832	-134.900	0.657	-25.600	0.118	25.500	0.633	-166.400	0.954	7.457

S-Parameters include 0.0010" (24.5 μm) gold bond wires as follows:
 Gate, 2 wires, 1 per bond pad, 0.0265" (674 μm) long each wire
 Drain, 2 wires, 1 per bond pad, 0.0232" (590 μm) long each wire
 Source, 4 wires, 2 per side, 0.0092" (234 μm) long each wire

OUTLINE DIMENSIONS

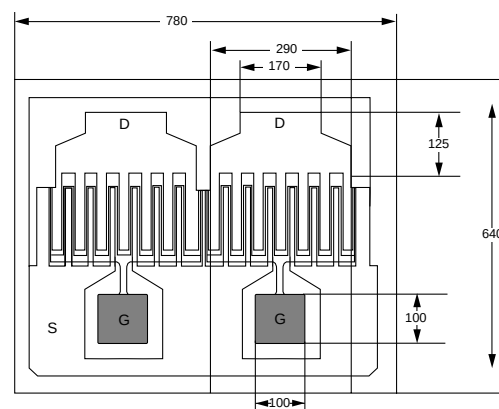
PACKAGE OUTLINE 99

(Units in mm)



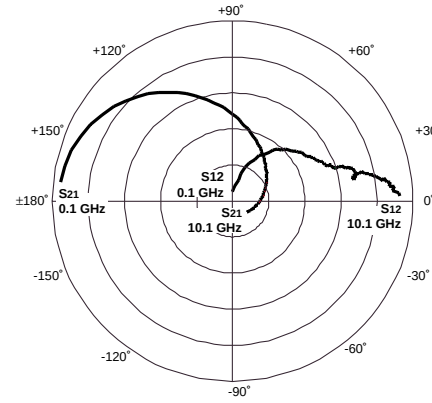
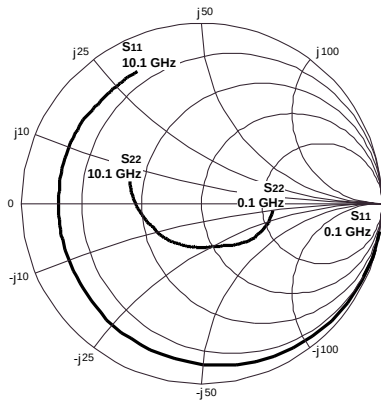
CHIP (00)

(Units in μm)



Die Thickness 140

TYPICAL SCATTERING PARAMETERS (T_A = 25 °C)



S₂₁ MAG:
2.0 / DIV., 10.0 FS
S₁₂ MAG:
0.02 / DIV., 0.1 FS

NE 8500100 (1 Cell)

V_{DS} = 10 V, I_{DS} = 100 mA

FREQUENCY	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹
GHZ	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)
0.10	1.000	-8.800	9.587	173.800	0.005	88.900	0.396	-4.900	-0.020	32.827
0.20	0.995	-17.500	9.496	168.200	0.008	83.000	0.393	-8.700	0.043	30.745
0.50	0.970	-42.300	8.950	151.600	0.020	69.500	0.377	-19.900	0.147	26.508
1.00	0.915	-77.700	7.570	128.200	0.034	53.100	0.338	-35.800	0.279	23.476
1.50	0.868	-104.800	6.243	109.800	0.042	42.600	0.302	-48.400	0.406	21.721
2.00	0.839	-125.600	5.191	95.300	0.047	34.000	0.274	-59.000	0.524	20.432
2.50	0.813	-141.500	4.347	83.100	0.050	29.400	0.256	-67.500	0.675	19.392
3.00	0.803	-154.500	3.724	71.700	0.052	26.000	0.246	-76.600	0.789	18.550
3.50	0.798	-165.700	3.284	61.900	0.054	23.200	0.243	-85.900	0.874	17.840
4.00	0.797	-175.300	2.894	53.300	0.056	21.200	0.243	-95.000	0.953	17.133
4.50	0.796	-176.400	2.564	44.800	0.057	20.500	0.247	-104.000	1.055	15.097
5.00	0.798	-168.800	2.308	34.800	0.059	18.200	0.253	-113.200	1.115	13.864
5.50	0.799	-161.700	2.115	27.100	0.061	17.800	0.260	-122.000	1.164	12.943
6.00	0.801	-155.400	1.912	20.500	0.064	17.900	0.272	-130.800	1.206	12.013
6.50	0.803	-149.400	1.729	12.700	0.067	15.900	0.284	-139.300	1.251	11.101
7.00	0.804	-143.500	1.611	4.100	0.070	11.500	0.296	-148.700	1.264	10.528
7.50	0.800	-138.300	1.478	-1.900	0.068	10.700	0.305	-156.000	1.456	9.366
8.00	0.800	-133.800	1.342	-8.200	0.070	12.600	0.323	-163.400	1.549	8.462
8.50	0.802	-129.300	1.247	-16.200	0.075	11.900	0.344	-171.400	1.511	7.988
9.00	0.805	-125.000	1.182	-23.200	0.081	10.000	0.366	-179.300	1.418	7.798
9.50	0.811	-120.800	1.099	-29.200	0.086	6.900	0.390	-172.500	1.357	7.498
10.00	0.816	-116.800	1.004	-35.200	0.092	2.800	0.414	-164.300	1.312	7.030

S-parameters include 0.0010" (25.4 μm) gold bond wires as follows:

Gate, 1 wire, 1 per bond pad, 0.0245" (619 μm) long each wire

Drain, 1 wire, 1 per bond pad, 0.0248" (631 μm) long each wire

Source, 2 wires, 2 per side, 0.0090" (229 μm) long each wire

Note:

1. Gain calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

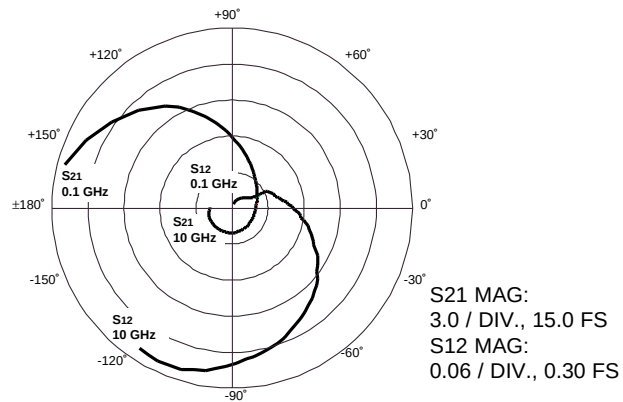
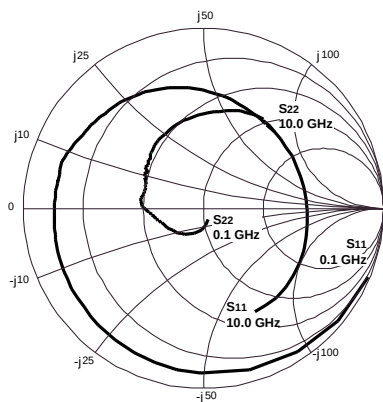
MSG = Maximum Stable Gain

NE8500199 LARGE SIGNAL IMPEDANCES

FREQ (GHz)	Z _{IN} (ohm)	Z _{OUT} (ohm)
5.90	7.08 - j 20.24	15.95 - j 5.70
6.20	8.37 - j 23.28	15.36 - j 8.11
6.40	16.11 - j 41.46	18.87 - j 19.33
6.50	9.30 - j 11.82	23.53 + j 3.06

Z_{IN} is the impedance of the input matching circuit as seen by the gate.

Z_{OUT} is the impedance of the output matching circuit as seen by the drain.

TYPICAL SCATTERING PARAMETERS (T_A = 25 °)

NE 8500199

V_{DS} = 10 V, I_{DS} = 200 mA

FREQUENCY GHZ	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹ (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
0.10	0.990	-22.700	14.418	165.500	0.007	70.100	0.065	-64.600	0.097	33.138
0.50	0.916	-91.100	10.211	123.300	0.024	47.700	0.175	-126.400	0.300	26.289
1.00	0.869	-132.100	6.444	94.800	0.031	33.600	0.221	-149.100	0.558	23.178
1.50	0.851	-152.900	4.610	76.600	0.034	29.000	0.241	-159.200	0.797	21.322
2.00	0.840	-166.100	3.591	61.900	0.038	28.100	0.260	-165.600	0.970	19.754
2.50	0.831	-175.900	2.975	49.100	0.042	26.700	0.278	-170.800	1.098	16.592
3.00	0.826	-176.000	2.601	37.300	0.047	25.400	0.296	-174.600	1.129	15.244
3.50	0.824	-168.800	2.341	26.000	0.053	27.400	0.313	-177.800	1.109	14.437
4.00	0.829	-161.000	2.127	13.400	0.066	25.400	0.345	-176.300	0.915	15.082
4.50	0.803	-152.500	1.963	3.400	0.075	15.200	0.337	-166.200	1.007	13.658
5.00	0.784	-144.700	1.929	-8.600	0.084	9.300	0.340	-159.800	0.984	13.611
5.50	0.767	-135.900	1.916	-20.700	0.097	3.100	0.358	-154.200	0.891	12.956
6.00	0.751	-125.800	1.928	-33.500	0.113	-4.800	0.381	-149.500	0.767	12.320
6.50	0.726	-114.100	1.951	-47.200	0.130	-13.200	0.396	-144.200	0.697	11.763
7.00	0.689	-100.200	1.957	-62.400	0.149	-23.900	0.402	-137.100	0.678	11.184
7.50	0.649	-83.400	2.013	-78.800	0.177	-36.800	0.431	-129.400	0.601	10.559
8.00	0.604	-63.200	2.067	-96.600	0.206	-51.800	0.465	-117.200	0.557	10.015
8.50	0.577	-37.000	2.102	-115.500	0.232	-68.000	0.500	-102.700	0.526	9.571
9.00	0.571	5.900	2.072	-135.700	0.253	-84.700	0.534	-87.200	0.512	9.133
9.50	0.611	-28.500	2.030	-157.900	0.277	-103.200	0.577	-69.700	0.464	8.650
10.00	0.631	-62.900	1.812	-177.300	0.280	-123.600	0.587	-47.000	0.513	8.110

Note:

1. Gain calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

MSG = Maximum Stable Gain

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